Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

ATTORNEY'S DKT NO.	APPLICATION NO.
033022-004	09/604,097
APPLICANT: Yukio SHAKUDA	
FILING DATE: June 27, 2000	GROUP: 6648

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U.S. PATENT DOCUMENTS

Examiner Initials	U.S. Patent Document Number	U.S. Patent Document Kind Code (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication (MM-DD-YYYY)

FOREIGN PATENT DOCUMENTS

Examiner Initials	Foreign Patent Document Number	Foreign Patent Document Kind Code (if known)	Country	Date of Publication (MM-DD-YYYY)	Translation Yes	Translation no
	6-268259		Japan	09-22-1994	X	
	7-312445		Japan	11-28-1995	X	
	2-229475		Japan	09-12-1990	X	

NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Include name of author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
	Blue Device Development Story (P1-6 and P10, ELECTRONICS, April 1999 issue) (with English Translation)
	Semiconductor Laser (issued on October 25, 1994), (P44-P45) (with English Translation)
	Device Physical Properties and Applications (P124-P125, The Fascination of Blue Light Emitting Device, issued on April 14, 1997) (with English Translation)

Examiner Signature		Date Considered	10/22/02

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. SEND TO: Assistant Commissioner for Patents, Washington, D.C. 20231.

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SHEET 1 OF 1

Substitute for form 1449A/PTO	ATTORNEY'S DKT NO. 033022-004	APPLICATION NO. 09/604,097
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	APPLICANT Yukio SHAKUDA	
	FILING DATE June 27, 2000	GROUP 2828

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U.S. PATENT DOCUMENTS

Examiner Initials	U.S. Patent Document Number	Kind Code (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication (MM-DD-YYYY)

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NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Include name of author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
JD	T. Nagatomo, et al., "Properties of $Ga_{1-x}In_xN$ Films Prepared by MOVPE", Japanese Journal of Applied Physics, Vol. 28, No. 9, August, 1989, pp. L1334-L1336 Blue Device Development Story (P1-6 and P10, ELECTRONICS, April 1999 issue) (with English Translation)
JD	K. Osamura, et al., "Fundamental Absorption Edge in GaN, InN and Their Alloys", Solid State Communications, Vol. 11, 1972, pp. 617-621 (No month)
JD	S. Yoshida, et al., "Properties of $Al_xGa_{1-x}N$ Films Prepared by Reactive Molecular Beam Epitaxy", J. Appl. Phys., Vol. 53, No. 10, October 1982
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JD	~~C. H. Carter, Jr.~~ I. Akasaki, et al., "MOVPE Growth Of High Quality $Al_xGa_{1-x}N/Ga_yIn_{1-y}N(x>0,y<1)$ Heterostructures for Short Wavelength Light Emitter", Mat. Res. So. Symp. Pro., Vol. 339, 1994 pages 443-452 (No month)
JD	L. Hrivnak, "Band Gap, Effective Masses, and Band Offsets in Lattice Matched Heterojunctions", Phys. Stat. Sol. (a), Vol. 128, K.89, 1991

Examiner Signature	James Ou	Date Considered	10/23/02

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